



JST04F-800SW 4A TRIACs

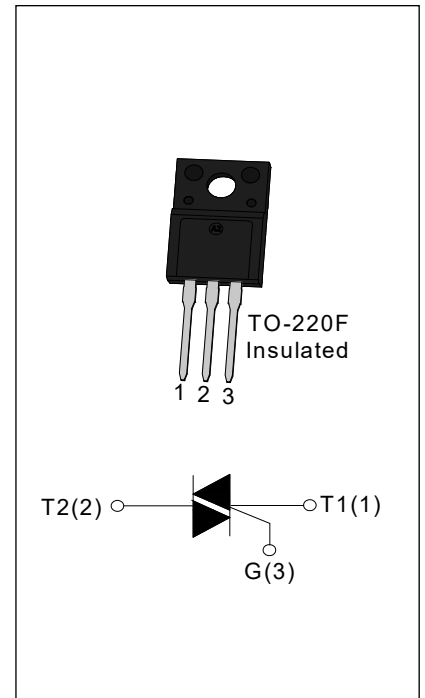
Rev.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST04F-800SW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. From all three terminals to external heatsink, JST04F-800SW provides a rated insulation voltage of 2000 V_{RMS}, complying with UL standards (Fileref:E252906). Package TO-220F is RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
V _{DRM} / V _{RRM}	800	V
I _{T(RMS)}	4	A



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T _{stg}	-40 - 150	°C
Operating junction temperature range		T _j	-40 - 125	°C
Repetitive peak off-state voltage (T _j =25°C)		V _{DRM}	800	V
Repetitive peak reverse voltage (T _j =25°C)		V _{RRM}	800	V
RMS on-state current	TO-220F(Ins) (T _c =100°C)	I _{T(RMS)}	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I _{TSM}	40	A
I ² t value for fusing (tp=10ms)		I ² t	8	A ² s
Critical rate of rise of on-state current (I _G = 2 × I _{GT})		di/dt	50	A/μs
Peak gate current		I _{GM}	4	A
Average gate power dissipation		P _{G(AV)}	1	W
Peak gate power		P _{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	10	mA
V_{GT}		I - II -III	MAX	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	20	mA
		II		35	
I_H	$I_T=100\text{mA}$		MAX	15	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	100	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=5.5\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.93	V
R_d	Dynamic resistance	$T_j=125^{\circ}\text{C}$	97	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	10	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.75	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220F(Ins)	3.0	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

<u>J</u>	<u>ST</u>	<u>04</u>	<u>F</u>	<u>-800</u>	<u>SW</u>	<u>-/</u>
JieJie Microelectronics Co.,Ltd	Triacs	$I_{T(RMS)}:4A$				Blank: Tube
		$F:TO-220F(Ins)$			$SW: I_{GT1-3} \leq 10mA$	
				$800:V_{DRM} / V_{RRM} \geq 800V$		

MARKING

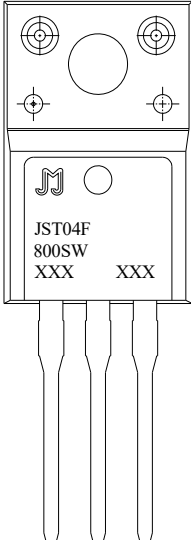
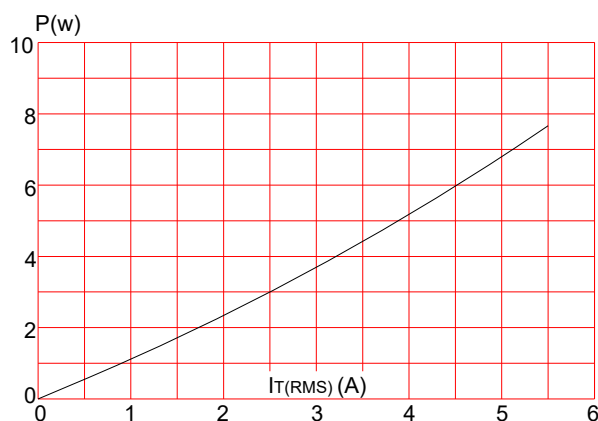
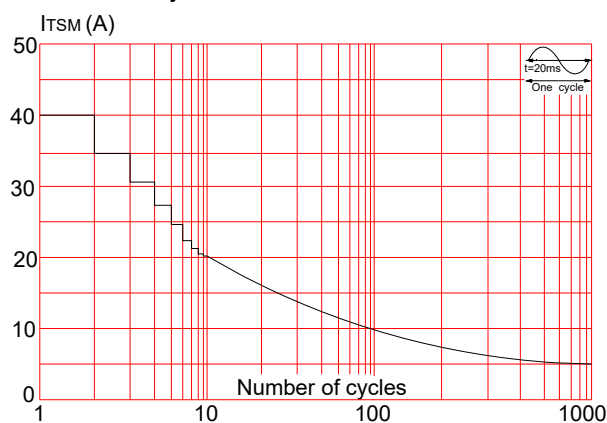
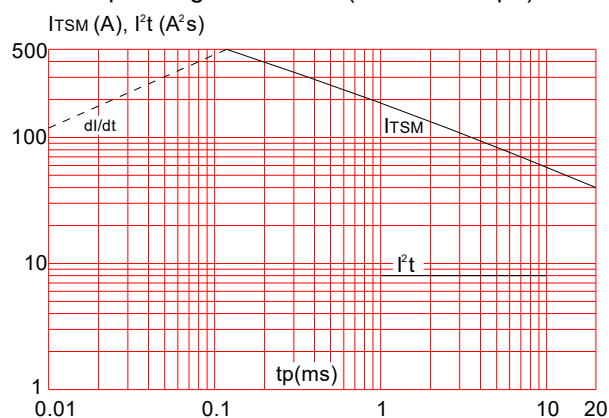
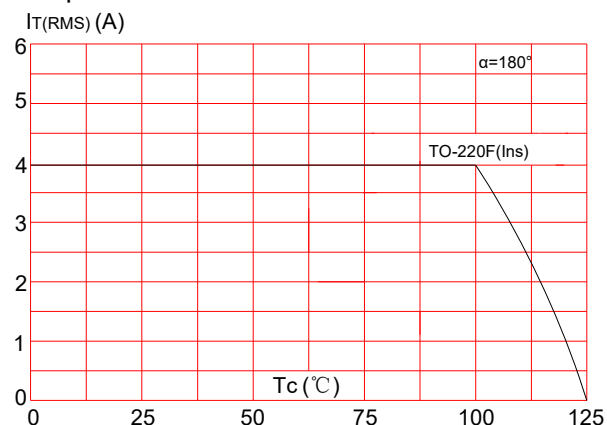
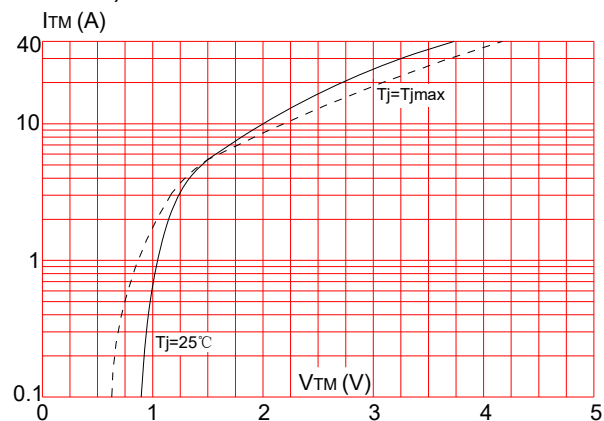
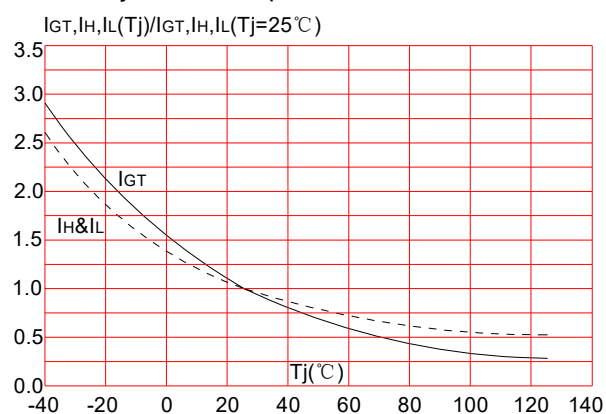
 JST04F 800SW XXX XXX	XXX XXX Year _____ Month _____ Production Code
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FIG.1: Maximum power dissipation versus RMS on-state current**FIG.3:** Surge peak on-state current versus number of cycles**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)**FIG.2:** RMS on-state current versus case temperature**FIG.4:** On-state characteristics (maximum values)**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

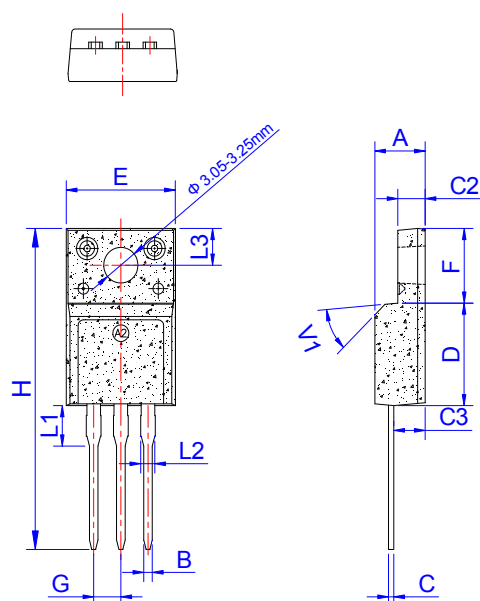
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST04F-800SW	800	10	TO-220F(Ins)	50	Tube

Document Revision History

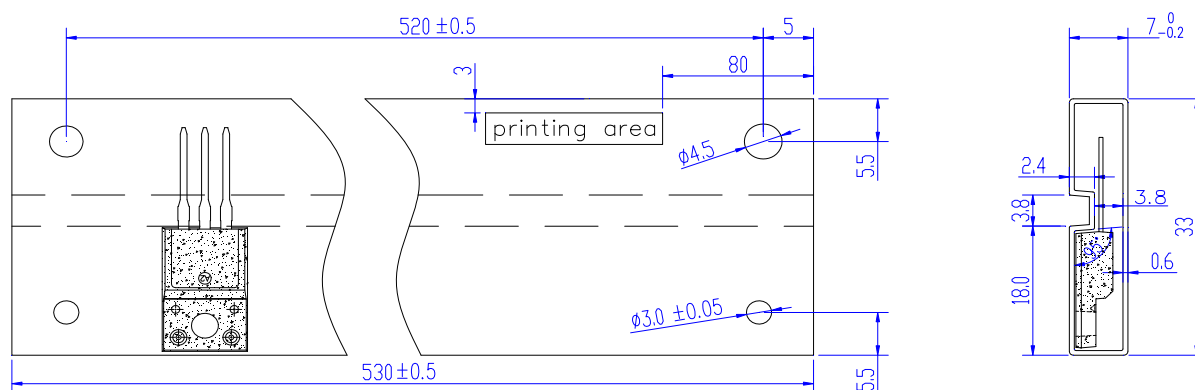
Date	Revision	Changes
Mar 27, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000



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